

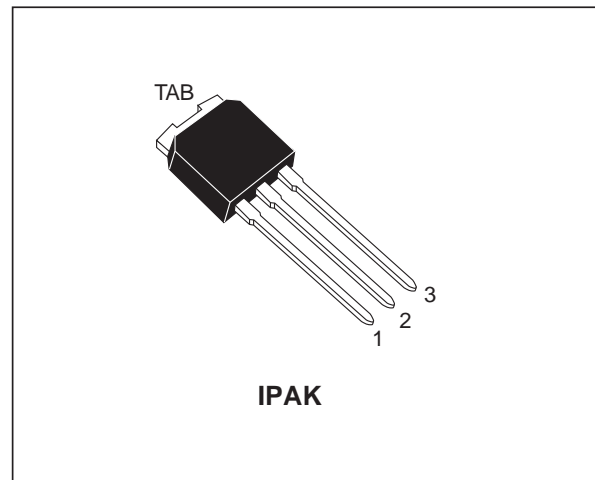
LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	8 A
V_{RRM}	30 V
$T_j(\text{max})$	150 °C
$V_F(\text{max})$	0.40 V

FEATURES AND BENEFITS

- LOW COST DEVICE WITH LOW DROP FORWARD VOLTAGE FOR LESS POWER DISSIPATION AND REDUCED HEATSINK
- OPTIMIZED CONDUCTION/REVERSE LOSSES TRADE-OFF WHICH LEADS TO THE HIGHEST YIELD IN THE APPLICATIONS



DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in IPAK, this device is especially intended for use as a Rectifier at the secondary of 3.3V SMPS or DC/DC units.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		7	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ\text{C} \quad \delta = 0.5$	8	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ $F = 1 \text{ kHz}$ square	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu\text{s}$ square	2	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum junction temperature		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS8L30H

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		1	mA
		$T_j = 100^\circ\text{C}$		15	40	
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$		0.49	V
		$T_j = 125^\circ\text{C}$		0.35	0.4	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$		0.63	
		$T_j = 125^\circ\text{C}$		0.48	0.57	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.23 \times I_{F(AV)} + 0.021 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

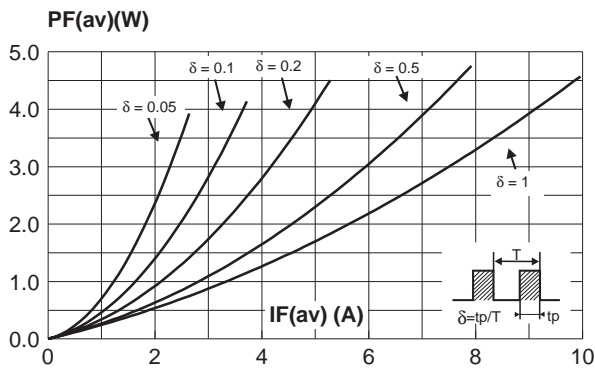


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

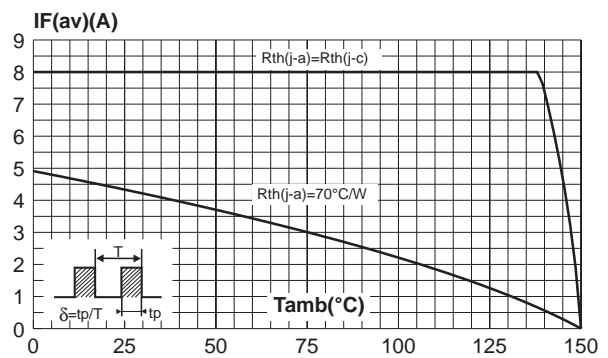


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values).

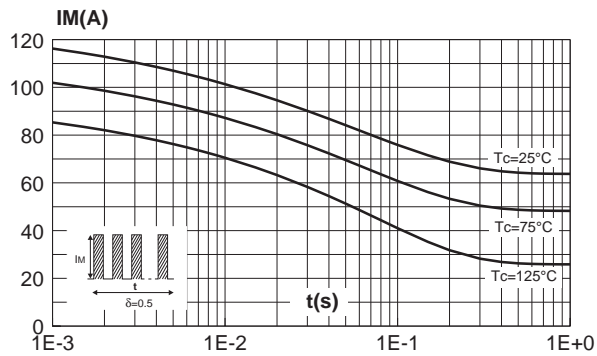


Fig. 4: Relative variation of thermal impedance junction to ambient versus pulse duration.

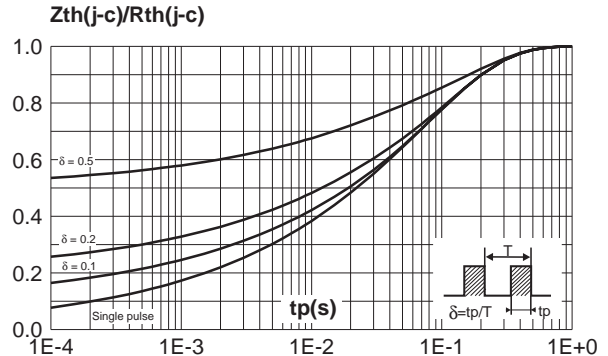


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

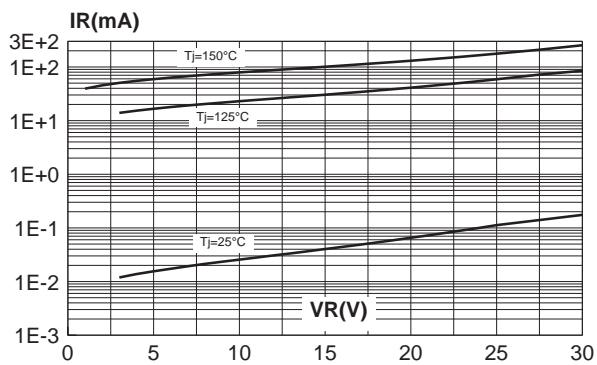


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).

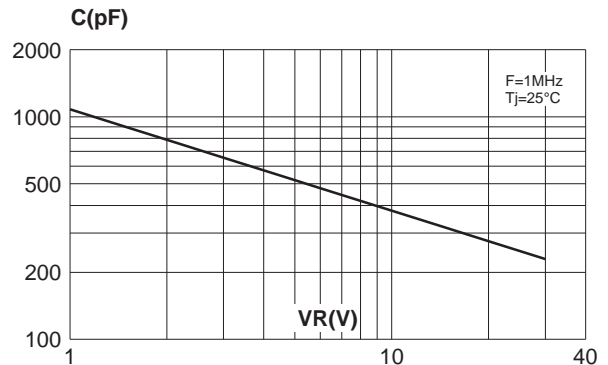
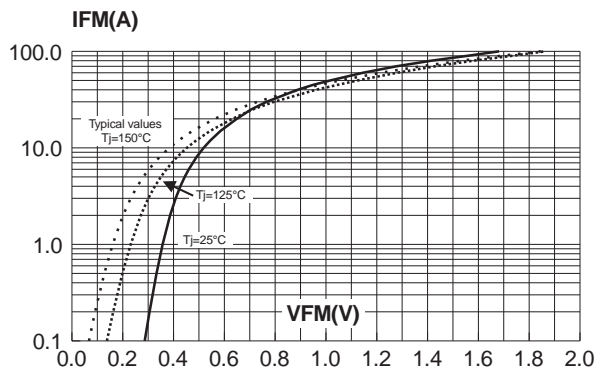
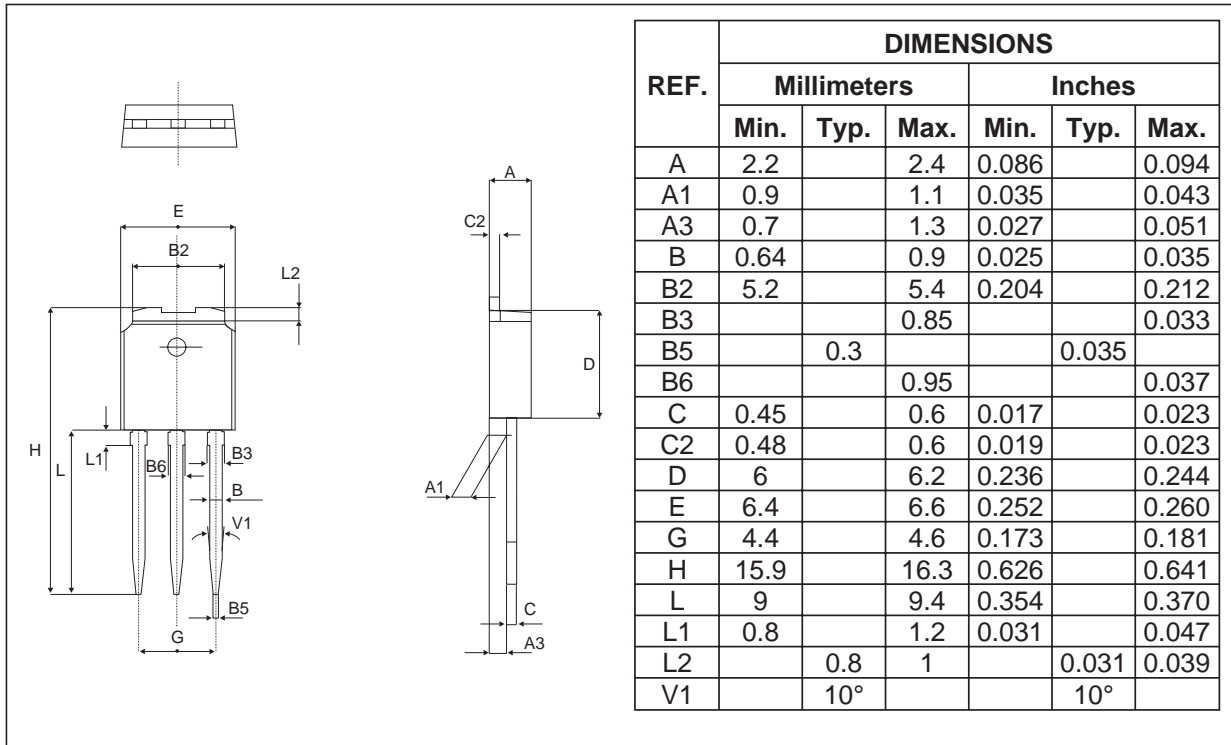


Fig. 7: Forward voltage drop versus forward current (maximum values).



STPS8L30H

PACKAGE MECHANICAL DATA IPAK



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS8L30H	ST LS30	IPAK	0.35g	75	Tube

- Epoxy meets UL94,V0

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